# Monday Morning, October 19, 2015

### Atom Probe Tomography Focus Topic Room: 230A - Session AP+AS+MC+MI+NS-MoM

### Atom Probe Tomography of Nanomaterials

**Moderator:** Daniel Perea, Pacific Northwest National Laboratory

8:20am AP+AS+MC+MI+NS-MoM1 Correlative Multi-scale Analysis of Nd-Fe-B Permanent Magnet, *Taisuke Sasaki, T. Ohkubo, K. Hono,* National Institute for Materials Science (NIMS), Japan **INVITED** (Nd,Dy)–Fe–B based sintered magnets are currently used for traction motors and generators of (hybrid) electric vehicles because of their excellent combination of maximum energy product and coercivity. However, there is a strong demand to achieve high coercivity without using Dy due to its scarce natural resources and high cost. In Nd-Fe-B sintered magnets, thin Nd-rich grain boundary (GB) phase is a key microstructural feature affecting the coercivity. Although Nd-rich phases, e.g. Nd-rich oxides and metallic Nd, located at grain boundary triple junctions affect the formation of the Nd-enriched grain boundary phase during post-sinter annealing, their phase constitution, distribution and orientation relationships are still under debate.

This presentation will introduce examples of advanced characterization works to establish the global microstructural feature that controls the coercivity of Nd-Fe-B sintered magnets, e.g. the clarification of phase constitution and distribution of Nd-rich phases at the grain boundaries by correlative SEM and TEM characterization, and the identification of he structure and chemistry of thin Nd-rich grain boundary phases by high resolution HAADF-STEM and 3D atom probe. We found the coercivity decrease by carbon impurity can be explained by the decrease in the RE (RE: Rare earth) content in the thin Nd-rich grain boundary phase.

#### 9:00am AP+AS+MC+MI+NS-MoM3 Atom-Probe Tomography of Materials with Dimensions in the Nanometer Range, Dieter Isheim, Northwestern University INVITED

Nanometer-sized materials and particles seem to naturally lend themselves for investigation by atom-probe tomography (APT) which provides analytical imaging with subnanometer-scale spatial resolution in three dimensions. The material's characteristic dimensions may already be close to the one required to produce the electric field necessary for analysis by field-evaporation in an atom-probe tomograph and thus analysis seems straight forward. In practice, however, controlled manipulation and positioning of these nanoparticles or nanowires for APT analysis proves challenging since the support structure of an APT tip must be strong enough to resist the mechanical stresses exerted by the high electric fields involved. Additionally, the nanoparticles should ideally not be altered or damaged in the preparation process. These requirements can be met by modern processing techniques that combine suitable deposition methods for packaging nanoparticles in structures that are either ready for analysis, or suitable for subsequent APT tip preparation by a standard technique. Focused-ion-beam (FIB) microscopes equipped with a micro- or nanomanipulator and gas injection systems for electron- or ion-beam induced deposition provide a versatile platform for packaging, cutting, joining, and manipulating nanostructured materials, and thus to capture and target nanoparticles or specific microstructural features for APT analysis. This presentation explores these techniques to characterize a variety of nanometer sized and nanostructured materials, including nanodiamond particles and catalytically grown silicon nanowires.

#### 9:40am AP+AS+MC+MI+NS-MoM5 Exploring Atom Probe Tomography for Energy Storage and Conversion Materials, *Pritesh Parikh*, University of California, San Diego, *A. Devaraj*, Pacific Northwest National Laboratory, *S. Meng*, University of California, San Diego

The Sun forms the largest and most abundant source of energy on earth, yet it is not exploited to its full potential. Solar energy is a burgeoning field with a real chance to replace fossil fuels. The intermittent presence of sunlight can be mitigated by combining energy conversion devices such as solar panels with energy storage devices, namely Li ion batteries. A true solution is possible with the integration of both solar panels and batteries. With the general impetus towards adopting renewable sources for large scale energy storage and supply, fundamental studies on solar panels and batteries will provide new clues to design the next generation of energy devices. A Perovskite solar cell is one such technology that has the potential of high efficiency and low processing costs but a clear understanding of the role of different materials and their individual interactions is still lacking. The ability to identify and understand interfaces and multiple layers in a complex device such as solar cells and batteries is the need of the hour. Here we report on laser assisted atom probe tomography of energy storage and conversion devices to identify the spatial distribution of the elements comprising the various layers and materials. Recent progress and significant challenges for preparation and study of perovskite solar cells and battery materials using laser assisted atom probe tomography will be discussed. This opens up new avenues to understand complex mutli-layer systems at the atomic scale and provide a nanoscopic view into the intricate workings of energy materials.

#### 10:00am AP+AS+MC+MI+NS-MoM6 Atom Probe Tomography of Ptbased Nanoparticles, *Katja Eder*, *P.J. Felfer*, *J.M. Cairney*, The University of Sydney, Australia

Pt nanoparticles are commonly used as catalysts in fuel cells. There are a lot of factors which influence the activity of a catalyst, including the surface structure and geometry [1], d-band vacancy of the metal catalyst [2], the type of metal oxide support [3] and the oxidation state of the surface [4]. It is not yet fully understood in which way these factors influence the activity of the catalyst, since it is experimentally very difficult to get atomic scale information about the distribution of the atoms within such particle with conventional methods like transmission electron microscopy (TEM), scanning electron microscopy (SEM), scanning tunnelling microscopy (STM) and others. Models available which try to explain the structureactivity relationships therefore vary widely and there is much debate in the scientific literature about the underlying mechanisms of catalysis. For this reason it is crucial to conduct more research with methods that are able to obtain chemical information with a resolution on the atomic scale. In the past few years atom probe tomography (APT) has successfully been used in several studies to analyse nanoparticles [4-6]. APT provides a 3D reconstruction of the original specimen, which gives information about the chemical composition and the microstructure at a very high resolution. This method will enable us to have a closer look at the surface and interfaces as well as the composition of individual nanoparticles and solute atoms. In this talk we will present APT results of Pt nanoparticles, describing our efforts to prepare specimens with a reasonable yield and improved throughput compared to earlier studies, as well as some of the approaches used to overcome the difficulties that this challenge presents.

[1] A.R. Tao, S. Habas, P. Yang, Small, 4 (2008) 310-325.

[2] M.-K. Min, J. Cho, K. Cho, H. Kim, Electrochimica Acta, 45 (2000) 4211-4217.

[3] T. Akita, M. Kohyama, M. Haruta, Accounts of chemical research, (2013).

[4] T. Li, E.A. Marquis, P.A.J. Bagot, S.C. Tsang, G.D.W. Smith, Catalysis Today, 175 (2011) 552-557.

[5] Y. Xiang, V. Chitry, P. Liddicoat, P. Felfer, J. Cairney, S. Ringer, N. Kruse, Journal of the American Chemical Society, 135 (2013) 7114-7117.

[6] D.J. Larson, A.D. Giddings, Y. Wu, M.A. Verheijen, T.J. Prosa, F. Roozeboom, K.P. Rice, W.M.M. Kessels, B.P. Geiser, T.F. Kelly, Ultramicroscopy, (2015).

10:40am AP+AS+MC+MI+NS-MoM8 APT & TEM Observations on Local Crystallization of NbO2 used in Switching Devices, J.-H. Lee, Pohang University of Science and Technology (POSTECH), Samsung Electronics, Republic of Korea, J.-B. Seol, C.-G Park, Pohang University of Science and Technology (POSTECH), National Institute for Nanomaterials INVITED Technology (NINT), Republic of Korea Threshold switching is the basis of electrical or thermal-driven phase change mechanism of oxide layer. That is, some oxide can change their conductivity from the level of insulators to that of metals with above certain current density. Although the mechanism responsible for threshold switching is not fully understood at present, it can be used as a switching device for the solution of sneak leakage problem. In order to apply the bipolar switching materials as the active layer of Resistive-switching Random Access Memory (RRAM), selection device which can minimize the sneak leakage current is needed. Among various candidates, we chose Nb-oxide for the selection device due to its superior compatibility with semiconductor structure. We have elucidated the mechanism of threshold switching of the amorphous NbO2 layer by using in-situ transmission electron microscopy (TEM) technique combined with atom probe tomography (APT).

In this study, we proved that through an ex-situ experiment using TEM the threshold switching of amorphous NbO<sub>2</sub> accompanies local crystallization. The change in I-V characteristics after electroforming was examined by evaluating the concentration profile. APT combined with in-situ TEM probing technique was performed to understand the threshold switching in

amorphous NbO<sub>2</sub>. The local crystallization in amorphous NbO<sub>2</sub> was validated by the observed difference in time-of-flight (ToF) between amorphous and crystalline NbO<sub>2</sub>. We concluded that the slower ToF of amorphous NbO<sub>2</sub> (a-NbO<sub>2</sub>) compared to that of crystalline NbO2 (c-NbO<sub>2</sub>) is due to the resistivity difference and trap-assisted recombination.

#### 11:20am AP+AS+MC+MI+NS-MoM10 Correlating Atom Probe Tomography with High-Resolution Scanning Transmission Electron Microscopy and Micro-Photoluminescence Spectroscopy: The Case of III-Nitride Heterostructures, *Lorenzo Rigutti*, University of Rouen INVITED

Correlating two or more microscopy techniques on the same nanoscale object may yield a relevant amount of information, which could not be achieved by other means. In this contribution, we present several results of correlated studies of micro-photoluminescence ( $\mu$ -PL), high-resolution scanning transmission electron microscopy (HR-STEM) and laser-assisted atom probe tomography (APT) on single nano-objects containing AlGaInN quantum well and quantum dot systems. We will show how this approach can be applied to the study of heterostructure interface definition, presence of defects, carrier localization and optical emission in III-N quantum confined systems [1]. Furthermore, we will show how the use of complementary techniques may be extremely helpful for a correct interpretation of atom probe results [2]. The possible implementation of micro-photoluminescence as an in-situ technique within the atom probe itself will finally be discussed [3].

- [1] L. Rigutti et al., Nano letters (2014), 14, 107-114.
- [2] L. Mancini et al. J. Phys. Chem. C (2014) 118, 24136-24151.
- [3] L. Rigutti et al., Ultramicroscopy (2013), 132, 75-80.

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